



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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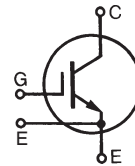


$$V_{CES} = 600V$$

$$I_{C110} = 170A$$

$$V_{CE(sat)} \leq 1.30V$$

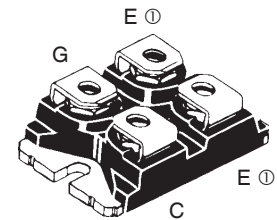
Ultra-Low-Vsat PT IGBT for
up to 5kHz Switching



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	320	A
I_{C110}	$T_C = 110^\circ C$	170	A
I_{LRMS}	Terminal Current Limit	200	A
I_{CM}	$T_C = 25^\circ C$, 1ms	1200	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 1\Omega$	$I_{CM} = 320$	A
(RBSOA)	Clamped Inductive Load	@ $0.8 \cdot V_{CES}$	
P_C	$T_C = 25^\circ C$	735	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
V_{ISOL}	50/60Hz	$t = 1min$	2500 V~
	$I_{ISOL} \leq 1mA$	$t = 1s$	3000 V~
M_d	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque (M4)	1.3/11.5	Nm/lb.in
Weight		30	g

SOT-227B, miniBLOC

E153432



G = Gate, C = Collector, E = Emitter

⓪ Either Emitter Terminal Can Be Used
as Main or Kelvin Emitter

Features

- Optimized for Low Conduction Losses
- High Avalanche Capability
- Isolation Voltage 3000 V~
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

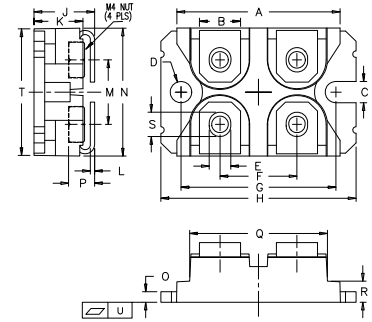
Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1mA$, $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 4mA$, $V_{CE} = V_{GE}$	3.0		5.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			150 μA
				1.5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 400 nA
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1 $I_C = 320A$	1.05	1.30	V
		1.46		V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 1	70	125	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		18	nF
C_{oes}			985	pF
C_{res}			150	pF
$Q_{g(on)}$	$I_C = 80\text{V}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		560	nC
Q_{ge}			94	nC
Q_{gc}			195	nC
$t_{d(on)}$	Resistive Load, $T_J = 25^\circ\text{C}$ $I_C = 80\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}$, $R_G = 1\Omega$		63	ns
t_r			68	ns
$t_{d(off)}$			290	ns
t_f			740	ns
$t_{d(on)}$	Resistive Load, $T_J = 125^\circ\text{C}$ $I_C = 80\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}$, $R_G = 1\Omega$		62	ns
t_r			77	ns
$t_{d(off)}$			330	ns
t_f			1540	ns
R_{thJC}			0.17	$^\circ\text{C/W}$
R_{thCK}		0.05		$^\circ\text{C/W}$

SOT-227B miniBLOC (IXGN)



M4 screws (4x) supplied

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

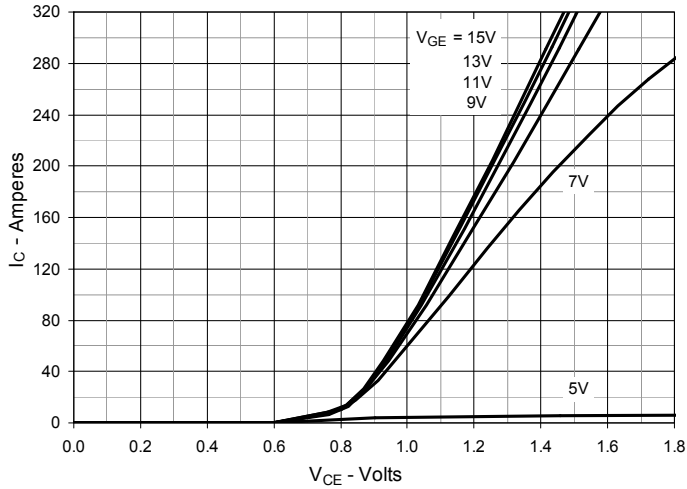
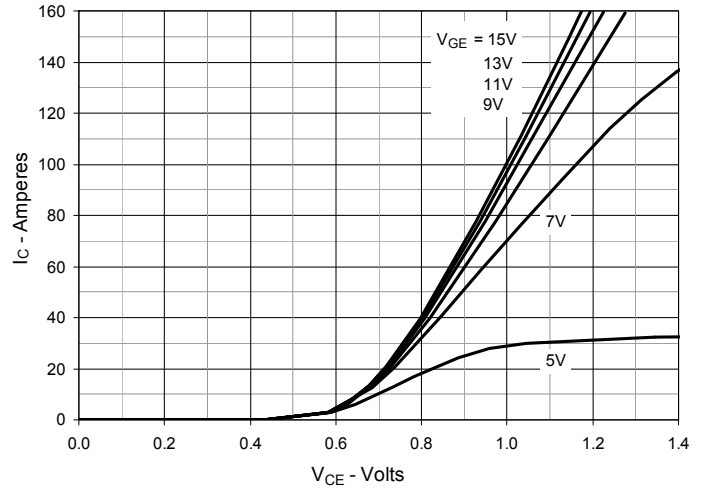
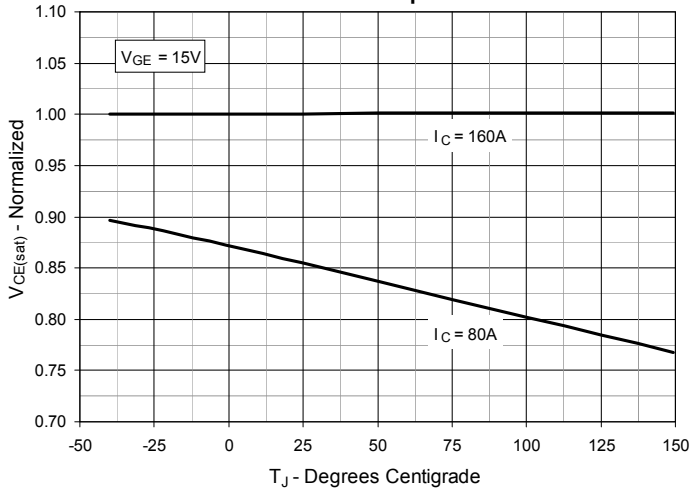
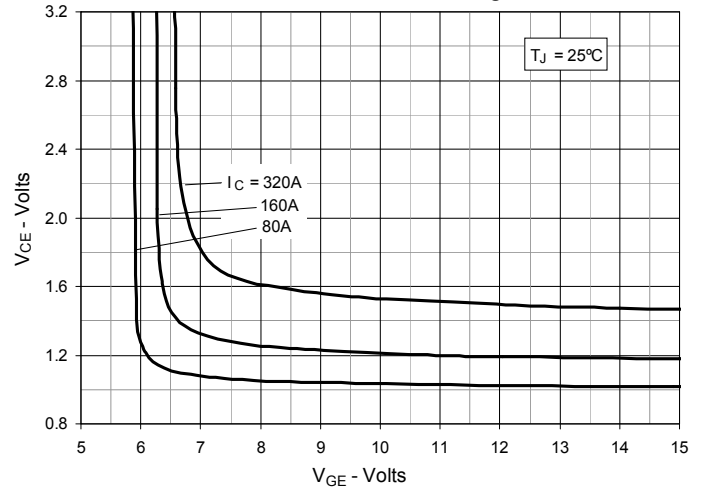
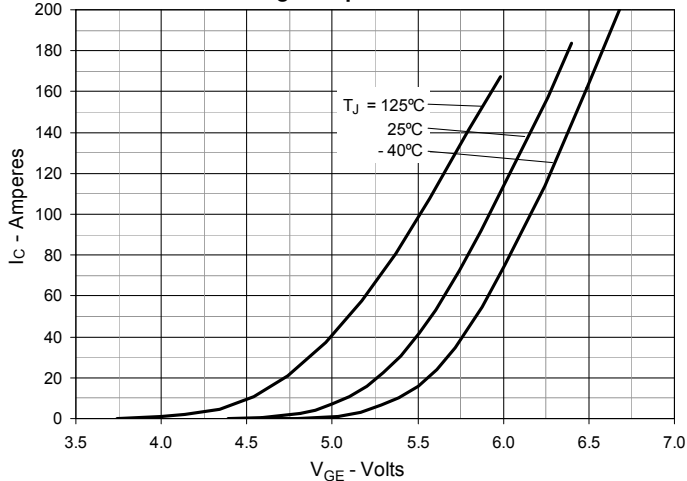
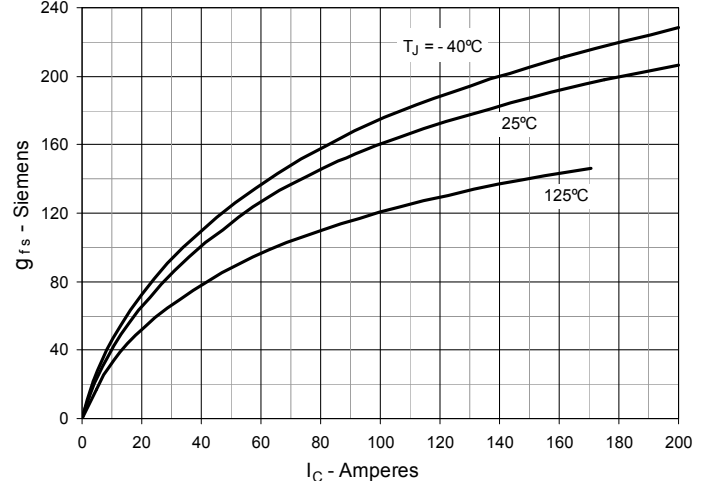
Fig. 1. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 3. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 4. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 5. Input Admittance

Fig. 6. Transconductance


Fig. 7. Gate Charge

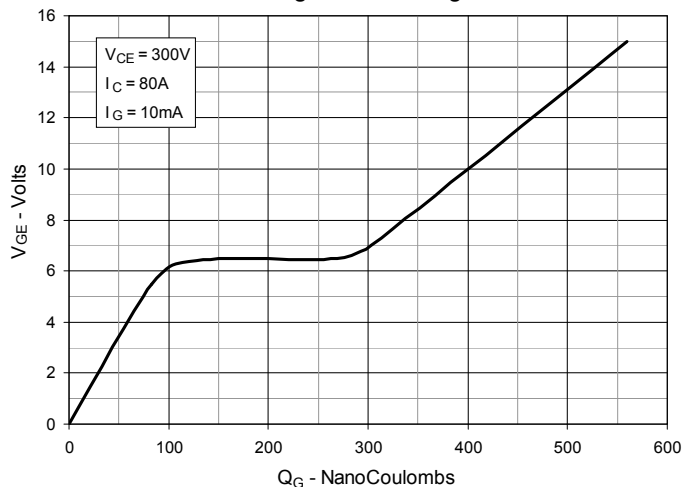


Fig. 8. Capacitance

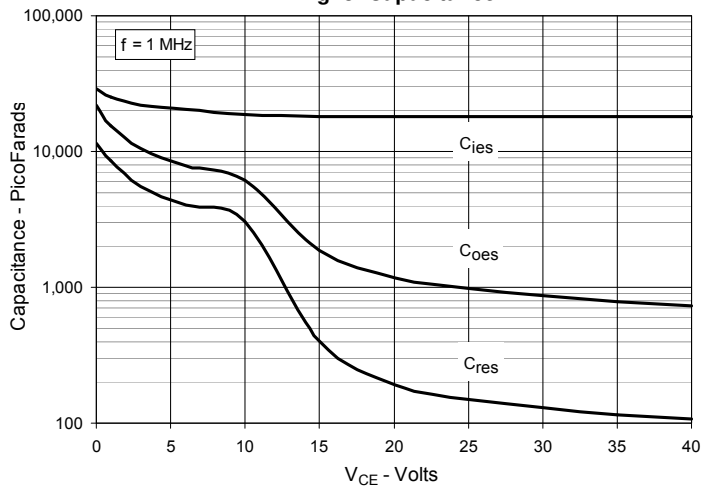


Fig. 9. Reverse-Bias Safe Operating Area

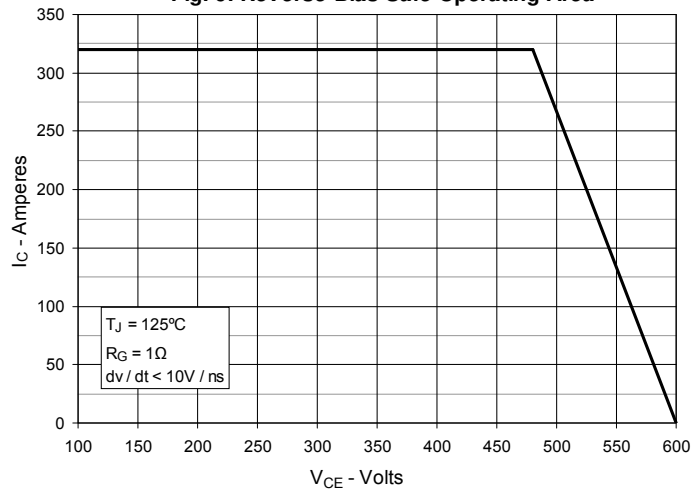


Fig. 10. Maximum Transient Thermal Impedance

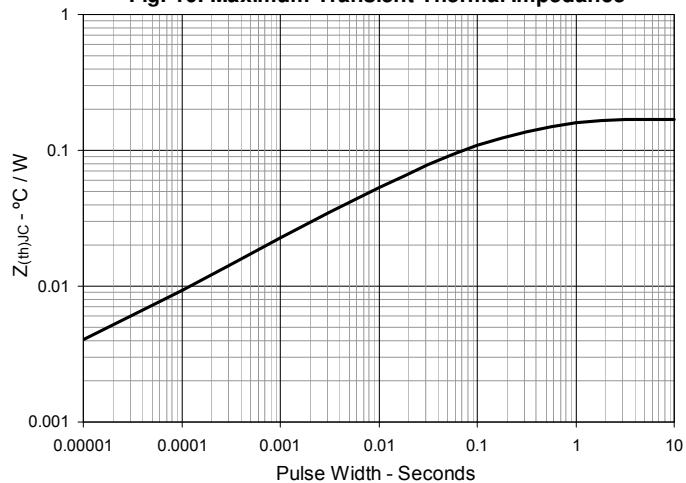


Fig.11. Resistive Turn-on Rise Time vs. Junction Temperature

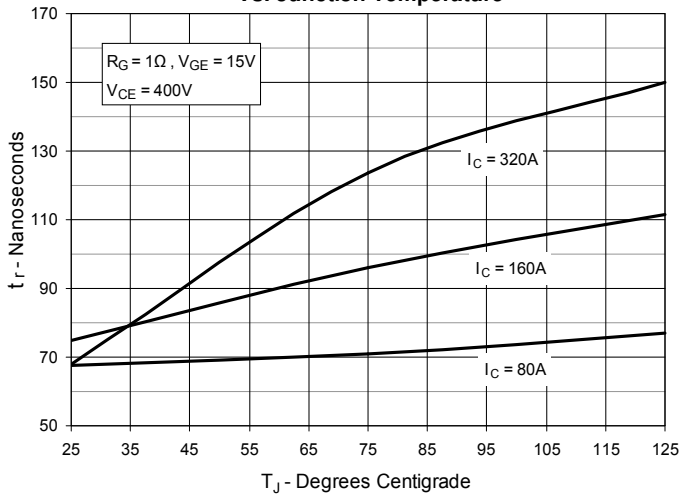


Fig. 12. Resistive Turn-on Rise Time vs. Collector Current

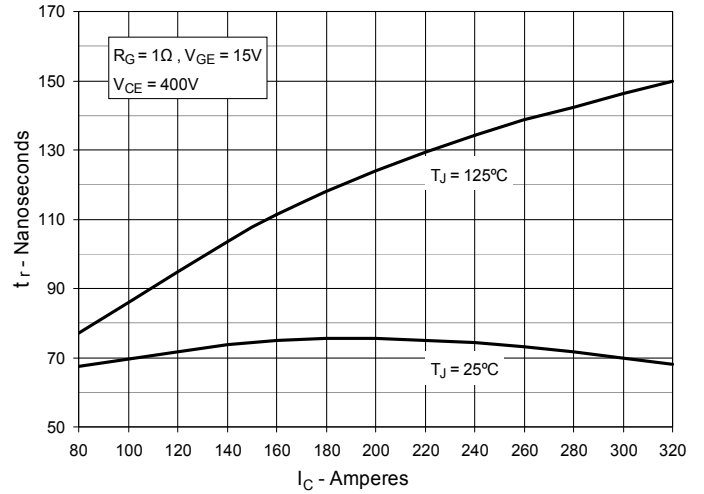


Fig. 13. Resistive Turn-on Switching Times vs. Gate Resistance

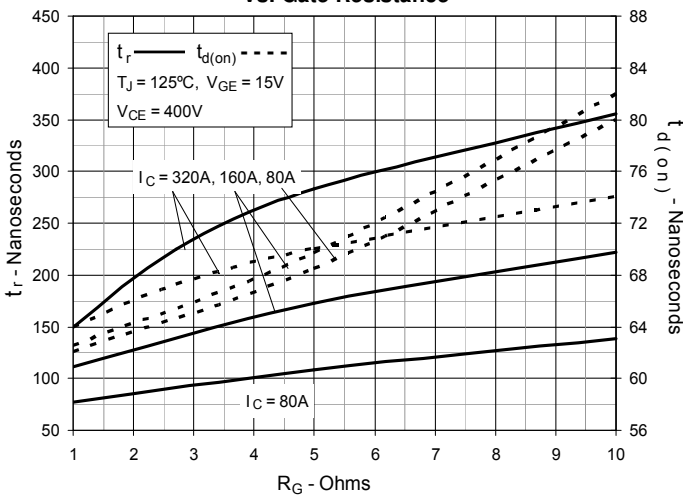


Fig. 14. Resistive Turn-off Switching Times vs. Junction Temperature

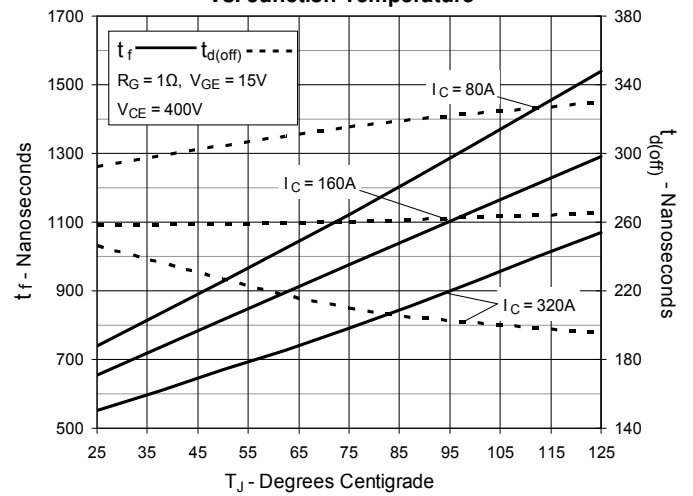


Fig. 15. Resistive Turn-off Switching Times vs. Collector Current

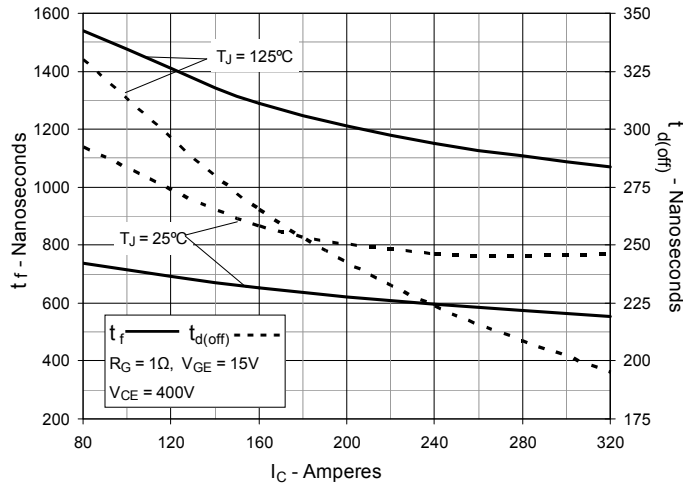


Fig. 16. Resistive Turn-off Switching Times vs. Gate Resistance

